1. General description

Ultrafast dual epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

2. Features and benefits

- · High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance
- Very low on-state loss
- · Soft recovery characteristic minimizes power consuming oscillations

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions Values					Unit	
Absolute	maximum rating							
V_{RRM}	repetitive peak reverse voltage		150					
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 115$ °C; both diodes conducting; Fig. 1; Fig. 2	20				А	
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s;	0.2				А	
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	8				kV	
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; per diode	20				А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125				А	
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137			А		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static ch	aracteristics							
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.72	0.85	V	
Dynamic	characteristics							
t _{rr} reverse recovery tim		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5		-	20	25	ns	
		I_F = 0.5 A to I_R = 1 A; T_j = 25 °C; measured at I_R = 0.25 A; step recovery; Fig. 6		-	10	20	ns	

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5. Pinning information

Table 2. Pinning information

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6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV32E-150	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYV32E-150	BYV32E-150

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		150	V
V_{RWM}	crest working reverse voltage		150	V
V_R	reverse voltage	DC	150	V
I _{O(AV)}	average output current	δ = 0.5; square-wave pulse; T _{mb} ≤ 115 °C; both diodes conducting; <u>Fig 1</u> ; <u>Fig 2</u>	20	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 115 °C$; per diode	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	125	А
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	137	А
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s; per diode	0.2	А
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs; per diode	0.2	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C
V _{ESD}	electrostatic discharge voltage	HBM; all pins; C = 250 pF; R = 1.5 kΩ	8	kV

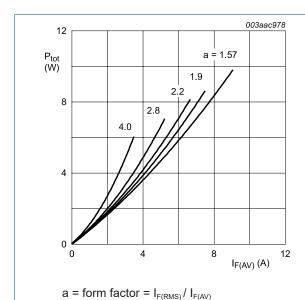


Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

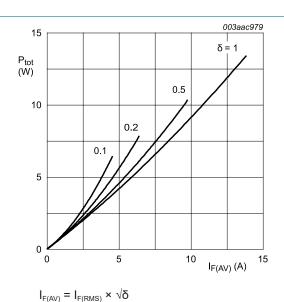


Fig. 2. Forward power dissipation as a function of average forward current; square waveform;

maximum values

BYV32E-150

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to		with heatsink compound; both diodes conducting	-	-	1.6	K/W
mo	mounting base	with heatsink compound; per diode; <u>Fig 3</u>	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	60	-	K/W

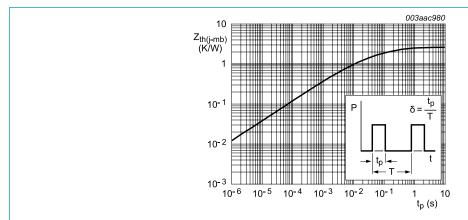


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

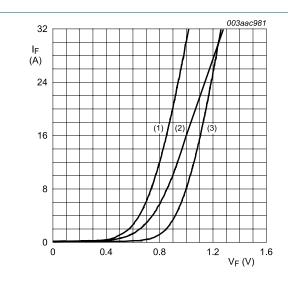
Dual rugged ultrafast rectifier diode, 20 A, 150 V

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.72	0.85	V
		I _F = 20 A; T _j = 25 °C	-	1	1.15	V
I _R	reverse current	V _R = 150 V; T _j = 25 °C	-	6	30	μΑ
		V _R = 150 V; T _j = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}$	-	8	12.5	nC
t _{rr} reverse recovery time		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ ramp recovery; } Fig. 5$	-	20	25	ns
		I_F = 0.5 A to I_R = 1 A; T_j = 25 °C; measured at I_R = 0.25 A; step recovery; Fig. 6	-	10	20	ns
V _{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	-	1	V

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(1) T_j = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

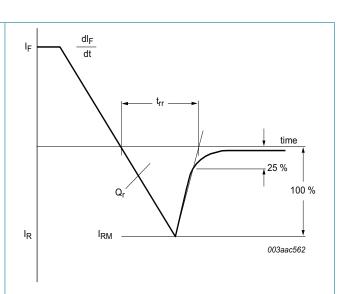


Fig. 5. Reverse recovery definitions; ramp recovery



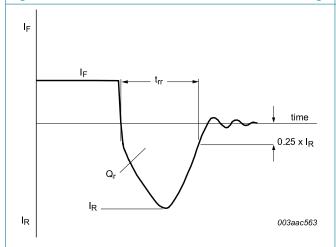


Fig. 6. Reverse recovery definitions; step recovery

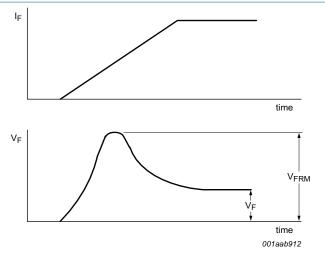


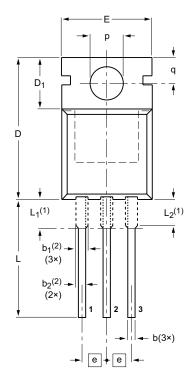
Fig. 7. Forward recovery definitions

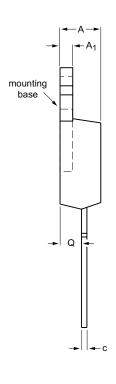
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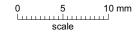
11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







DIMENSIONS (mm are the original dimensions)

UNIT	А	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES		ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

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12. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes					
BYV32E-150 v.5	20180307	Product specification	-	BYV32E-150_4					
Modifications:	Change from NXP version to WeEn version								
BYV32E-150_4	20090302	Product specification	-	BYV32E_SERIES_3					
Modifications:	 Modifications: The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. Package outline updated. Type number BYV32E-150 separated from data sheet BYV32E SERIES 3 								
BYV32E_SERIES_3	20010301	Product specification	-	BYV32E_SERIES_2					
BYV32E_SERIES_2	19980701	Product specification	-	BYV32EB_SERIES_1					
BYV32EB_SERIES_1	19960801	Product specification	-	-					

Dual rugged ultrafast rectifier diode, 20 A, 150 V

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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